TECHNICAL DATA
DATA SHEET D0124 REV. -

SILICON ZENER DIE

Features:

- **Zener Voltage 6.8V**
- **Withstand Large Surge Stresses**

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Power Dissipation	P_D	Derate above 25 °C	500	mW
Forward Voltage	V_F	@ IF=200mA, Pulse, T_J = 25 °C	1.1	V
Max. Junction Temperature	T_J	-	-65 to +175	°C
Max. Storage Temperature	T_{stg}	-	-65 to +175	°C

Electrical Characteristics @ T_J=25 °C:

Device	Zener voltage		Zener Impedence	Leakage Current	
	Nom. VZ ①	@ I_{ZT}	Max. Z_{ZT} @ I_{ZT}	Max. I_R @ V_R	
	Volts	mA	Ω	uA	Volts
1C754	6.8	20	5	2	4

Note: ①Vz Tolerance is ±5%

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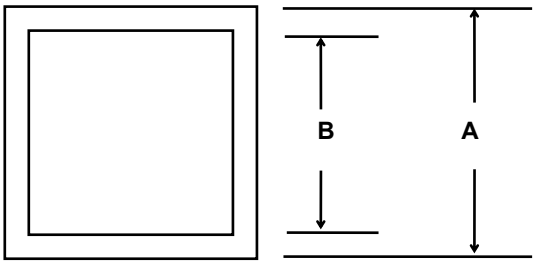
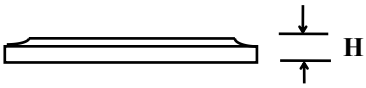
Mechanical Dimensions: In Inches (mm)





Bottom side metalization Au-4kÅ minimum

Top side metalization Al -25kÅ minimum

Bottom side is cathode, top side is anode

Dimension H =0.010 ± 0.002(0.25±0.051) (It can be customized according to customer requirements)

A	B
0.023 ± 0.002(0.58 ± 0.05)	0.015± 0.002(0.38 ± 0.05)